TOSHIBA Field Effect Transistor Silicon P-Channel MOS Type

# SSM3J111TU

# **High Speed Switching Applications**

• 2.5V drive

• Low on-resistance:  $R_{on}$  = 480m $\Omega$  (max) (@V<sub>GS</sub> = -4 V)  $R_{on}$  = 680m $\Omega$  (max) (@V<sub>GS</sub> = -2.5 V)

# **Absolute Maximum Ratings (Ta = 25°C)**

Characteristic		Symbol	Rating	Unit	
Drain-Source voltage		$V_{DS}$	-20	V	
Gate-Source voltage		V <sub>GSS</sub>	± 12	V	
Drain current	DC	I <sub>D</sub>	-1	Α	
	Pulse	I <sub>DP</sub>	-2		
Drain power dissipation		P <sub>D (Note 1)</sub>	800	mW	
		P <sub>D (Note 2)</sub>	500		
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	<b>−55~150</b>	°C	

Note:

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

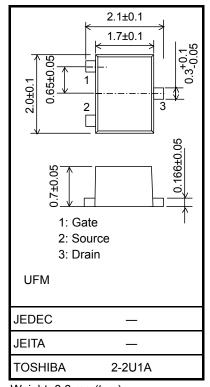
Note 1: Mounted on ceramic board.

 $(25.4 \text{ mm} \times 25.4 \text{ mm} \times 0.8 \text{ mm}, \text{ Cu Pad: } 645 \text{ mm}^2)$ 

Note 2: Mounted on FR4 board.

 $(25.4 \text{ mm} \times 25.4 \text{ mm} \times 1.6 \text{ mm}, \text{Cu Pad: } 645 \text{ mm}^2)$ 

#### Unit: mm



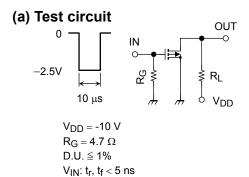
Weight: 6.6 mg (typ.)

# **Electrical Characteristics (Ta = 25°C)**

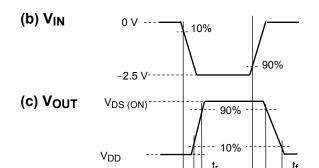
Characteristic		Symbol	Test Conditions	Min	Тур.	Max	Unit
Drain-Source breakdown voltage		V (BR) DSS	$I_D = -1 \text{ mA}, V_{GS} = 0$	-20	_	_	V
Drain cut-off curren	t	I <sub>DSS</sub>	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0	_	_	-1	μА
Gate leakage curre	nt	I <sub>GSS</sub>	$V_{GS} = \pm 12V, V_{DS} = 0$	_	_	±1	μА
Gate threshold volta	age	V <sub>th</sub>	$V_{DS} = -3 \text{ V}, I_D = -0.1 \text{ mA}$	-0.6	_	-1.1	V
Forward transfer ad	Imittance	Y <sub>fs</sub>	$V_{DS} = -3 \text{ V}, I_D = -0.3 \text{ A}$ (Note3)	0.6	1.2	_	S
Drain-Source on-resistance		R <sub>DS (ON)</sub>	$I_D = -0.3 \text{ A}, V_{GS} = -4.0 \text{ V}$ (Note3)	_	380	480	mΩ
			$I_D = -0.3 \text{ A}, V_{GS} = -2.5 \text{ V}$ (Note3)	_	530	680	
Input capacitance		C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0, f = 1 MHz	_	160	_	pF
Output capacitance		Coss	$V_{DS} = -10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	90	_	pF
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0, f = 1 MHz	_	25	_	pF
Switching time	Turn-on time	t <sub>on</sub>	$V_{DD} = -10 \text{ V}, I_D = -0.3 \text{ A},$	_	27	_	
	Turn-off time	t <sub>off</sub>	$V_{GS} = 0 \sim -2.5 \text{ V}, R_G = 4.7 \Omega$	_	43	_	ns
Drain-Source forward voltage		V <sub>DSF</sub>	$I_D = 1A$ , $V_{GS} = 0 V$ (Note3)	_	0.85	1.2	V

Note3: Pulse test

# **Switching Time Test Circuit**

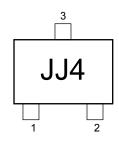


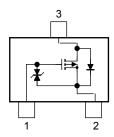
Common Source  $Ta = 25^{\circ}C$ 



# Marking

# **Equivalent Circuit (top view)**





#### **Precaution**

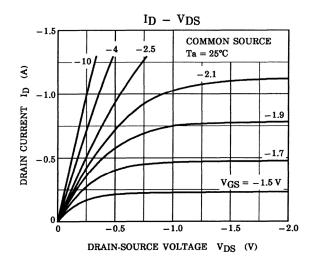
 $V_{th}$  can be expressed as the voltage between gate and source when the low operating current value is  $I_D$ =-0.1mA for this product. For normal switching operation,  $V_{GS\ (on)}$  requires a higher voltage than  $V_{th}$ , and  $V_{GS\ (off)}$  requires a lower voltage than  $V_{th}$ .

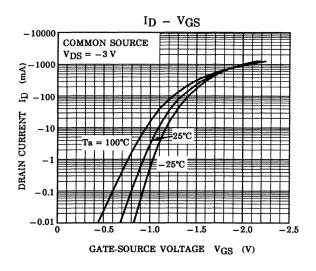
(The relationship can be established as follows:  $V_{GS (off)} < V_{th} < V_{GS (on)}$ )

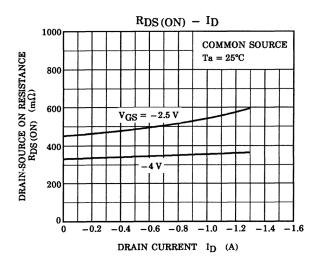
Take this into consideration when using the device.

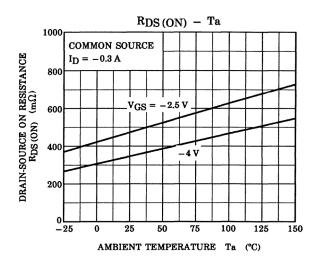
#### **Handling Precaution**

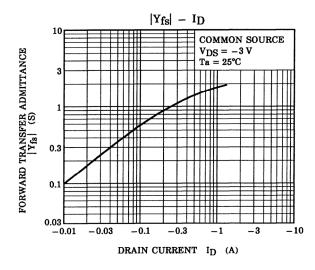
When handling individual devices which are not yet mounted on a circuit board, be sure that the environment is protected against electrostatic discharge. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

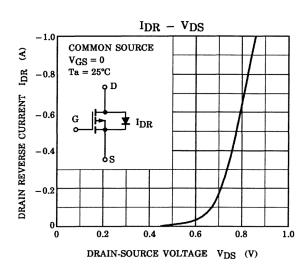


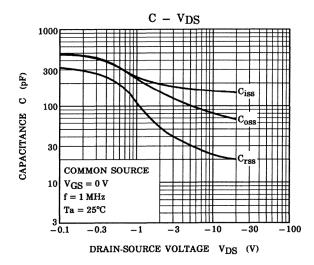


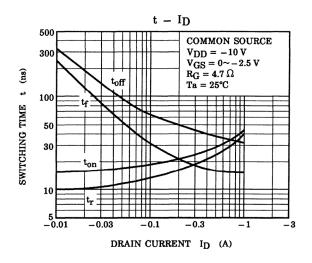


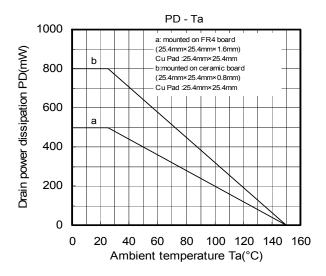


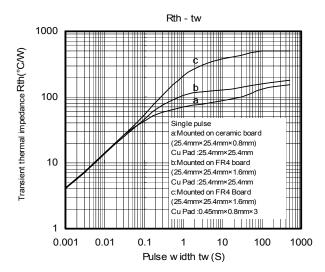












4

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20070701-EN GENERAL

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